

СПИСЪК

на избрани забелязани цитирания от чужди автори на публикациите на чл.кор. Ангел Сашев Попов (самоцитатите са изключени)

Номерата на цитираните работи са съгласно номерата на библиографската справка. Справката за цитатите е направена от следните бази данни въведени към момента за България: -“*ISI of Knowledge – Web of Science*” на информационната компания *Thomson & ISI*

-*Science Citation Index – CD-ROM*

-*SCOPUS* на издателство *ELSEVIER*

Представени са официални документи за намерените цитати и средния брой цитирания по години само в чужди списания. Тук не могат да бъдат забелязани цитирания в български списания, монографии, дисертации и т.н. Добавени са само някои случайно забелязани от нас цитати.

В долната таблица в колона 3 са събрани директните забелязани цитирания с общ брой **137**, а в колона 4 са събрани реферативни цитирания по горните бази данни с общ брой **1413**. Последните представляват броя цитирания от други автори на цитиращата статия в колона 3. От таблицата се вижда, че само някои цитиращи статии са цитирани от други автори

1	2	3	4
Номер по библ. списък	Цитирана статия	Цитира се от: (директни цитирания)	Брой цитирания(реферативни) на цитиращата статия
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3.	<i>Арнаудов Б., Попов А. “Полупроводникови излъчватели за влакнесто-</i>	1. Колев И. “ Оптоелектроника ”, УИ “Васил Априлов”-Габрово, 2004 , 230 с.	-

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